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Attorney Docket No. 50275-0014

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Christophe Pierrat, et al.

Group Art Unit No.: 2812

Examiner: NYA

Serial No.: 09/675,197

Filed on: September 29, 2000

For: DISSECTION OF EDGES WITH PROJECTION POINTS IN A FABRICATION LAYOUT FOR CORRECTING PROXIMITY EFFECTS

Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the documents cited on that form. It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The Examiner's attention is directed to the following co-pending U.S. Patent Applications:

U.S. patent application serial number 09/130,996, entitled "Visual Inspection and Verification System," filed on August 7, 1998;

U.S. patent application serial number 09/153,783, entitled "Design Rule Checking System and Method," filed on September 16, 1998;

U.S. patent application serial 09/544,798, entitled "Method and Apparatus for a Network Based Mask Defect Printability Analysis System," filed on April 7, 2000;

U.S. patent application serial number 09/154,415, entitled "Data Hierarchy Layout Correction and Verification Method and Apparatus," filed on September 16, 1998;

U.S. patent application serial number 09/154,397, entitled "Method and Apparatus for Data Hierarchy Maintenance in a System for Mask Description," filed on September 16, 1998; and

U.S. patent application serial number 09/632,080, entitled "General Purpose Shape-Based Layout Processing Scheme for IC Layout Modifications," filed on August 2, 2000,

which are directed to related technical subject matter. The identification of these U.S. Patent Applications is not to be construed as a waiver of secrecy as to these applications now or upon issuance of the present application as a patent. The Examiner is respectfully requested to consider the cited applications and the art cited therein during examination.

Throughout the pendency of this application, please charge any additional fees, including any required extension of time fees, and credit all overpayments to deposit account 50-1302. A duplicate of this sheet is enclosed.

Respectfully submitted,

HICKMAN PALERMO TRUONG & BECKER LLP

Dated: March 16, 2001

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, Washington, D. C. 20231 on March 20, 2001.
(Date of Deposit)

Jennifer Newell
(Typed or printed name of person mailing correspondence)

(Signature of person mailing correspondence)

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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